

Data sheet acquired from Harris Semiconductor **SCHS189**

CD74HC540, CD74HCT540, CD74HC541, CD74HCT541

High Speed CMOS Logic Octal Buffer and Line Drivers, Three-State

January 1998

Features

- CD74HC540, CD74HCT540 Inverting
- CD74HC541, CD74HCT541 Non-Inverting
- Buffered Inputs
- · Three-State Outputs
- . Bus Line Driving Capability
- Typical Propagation Delay = 9ns at V_{CC} = 5V, $C_L = 15pF, T_A = 25^oC$
- Fanout (Over Temperature Range)
 - Standard Outputs........... 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V (Max), V_{IH} = 2V (Min)$
 - CMOS Input Compatibility, $I_I \le 1\mu A$ at V_{OL} , V_{OH}

Description

The Harris CD74HC540 and CD74HCT540 are Inverting Octal Buffers and Line Drivers with Three-State Outputs and the capability to drive 15 LSTTL loads. The Harris CD74HC541 and CD74HCT541 are Non-Inverting Octal Buffers and Line Drivers with Three-State Outputs that can drive 15 LSTTL loads. The Output Enables (OE1) and (OE2) control the Three-State Outputs. If either OE1 or OE2 is HIGH the outputs will be in the high impedance state. For data output $\overline{\mathsf{OE1}}$ and $\overline{\mathsf{OE2}}$ both must be LOW.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC540E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT540E	-55 to 125	20 Ld PDIP	E20.3
CD74HC541E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT541E	-55 to 125	20 Ld PDIP	E20.3
CD74HC540M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT540M	-55 to 125	20 Ld SOIC	M20.3
CD74HC541M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT541M	-55 to 125	20 Ld SOIC	M20.3

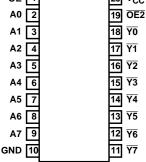
NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- 2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinouts

(PDIP, SOIC) TOP VIEW OE 1 20 V_{CC} A0 2 Α1

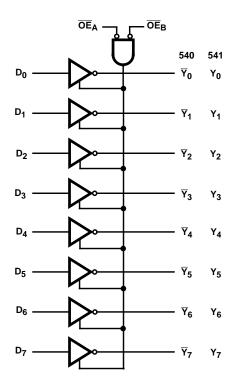
CD74HC540, CD74HCT540



CD74HC541, CD74HCT541 (PDIP, SOIC) TOP VIEW

OE1 1	20	v _{cc}
A0 2	19	OE2
A1 3	18	Y0
A2 4	17	Y 1
A3 5	16	Y2
A4 6	15	Υ3
A5 7	14	Y4
A6 8	13	Y5
A7 9	12	Y6
GND 10	11	Y7
	_	

Functional Diagram



TRUTH TABLE

	INPUTS	OUTPUTS				
OE1	OE2	An	540	541		
L	L	Н	L	Н		
Н	Х	Х	Z	Z		
Х	Н	Х	Z	Z		
L	L	L	Н	L		

NOTE:

H = HIGH Voltage Level
L = LOW Voltage Level

X = Don't Care

Z = High Impedance

Absolute Maximum Ratings

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (oC/W)
PDIP Package	. 125
SOIC Package	. 120
Maximum Junction Temperature	150 ⁰ C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300 ^o C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range, T _A 55°C to 125°C Supply Voltage Range, V _{CC}
HC Types
* *
HCT Types
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

		TEST CONDITIONS		V _{CC}	25°C			-40°C 1	O 85°C	-55°C T		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	(S)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES					-	-	-	-				
High Level Input	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	VoH	OH VIH OF VIL	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
omeo Edudo			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
112 20000			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
CIVICO LOUGS			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	II	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА

DC Electrical Specifications (Continued)

	TEST CONDITIONS			V _{CC}	25°C			-40°C 1	TO 85°C	-55°C T		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μΑ
Three- State Leakage Current	l _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	μА
HCT TYPES	•	•	•				•	•	•	•		
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{ОН}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lį	V _{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	μА
Quiescent Device Current	Icc	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μА
Three- State Leakage Current	l _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	Δl _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μА

NOTE: For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

HCT Input Loading Table

	UNIT LOADS							
INPUT	HCT540	HCT541						
A0 - A7	1	0.4						
OE2	0.75	0.75						
ŌE1	1.15	1.15						

NOTE: Unit load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360µA max. at 25°C.

Switching Specifications $C_L = 50pF$, Input t_r , $t_f = 6ns$

		TEST			25°C			C TO °C		C TO 5°C	UNITS
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Data to Outputs (540)	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	110	-	140	-	165	ns
			4.5	-	-	22	-	28	-	33	ns
		C _L = 15pF	5	-	9	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	19	-	24	-	28	ns
Data to Outputs (541)	t _{PLZ} , t _{PHZ}	C _L = 50pF	2	-	-	115	-	145	-	175	ns
			4.5	-	-	23	-	29	-	35	ns
		C _L = 15pF	5	-	9	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	20	-	25	-	30	ns
Output Enable and Disable	t _{PLZ} , t _{PHZ}	C _L = 50pF	2	-	-	160	-	200	-	240	ns
to Outputs (540)			4.5	-	-	32	-	40	-	48	ns
		C _L = 15pF	5	-	13	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	27	-	34	-	41	ns
Output Enable and Disable	t _{PLZ} , t _{PHZ}	C _L = 50pF	2	-	-	160	-	200	-	240	ns
to Outputs (541)			4.5	-	-	32	-	40	-	48	ns
		C _L = 15pF	5	-	14	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	23	-	29	-	35	ns
Output Transition Time	t _{THL} , t _{TLH}	C _L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C _I	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540)	C _{PD}	C _L = 15pF	5	-	50	-	-	-	=	-	pF
Power Dissipation Capacitance (Notes 4, 5) (541)	C _{PD}	C _L = 15pF	5	-	48	-	-	-	-	-	pF
HCT TYPES			•					•		•	•
Propagation Delay	t _{PHL} , t _{PLH}										
Data to Outputs (540)	1112, 1211	C _L = 50pF	4.5	-	-	24	-	30	-	36	ns
		C _L = 15pF	5	-	9	-	-	-	-	-	ns
Data to Outputs (541)	t _{PHL} , t _{PLH}	C _L = 50pF	4.5	-	-	28	-	35	-	42	ns
		C _L = 15pF	5	-	11	-	-	-	-	-	ns
Output Enable and Disable	t _{PLZ} , t _{PHZ}	C _L = 50pF	4.5	-	-	35	-	44	-	53	ns
to Outputs (540, 541)		C _L = 15pF	5	-	14	-	-	-	-	-	ns
Output Transition Time	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	Cl	C _L = 50pF	-	10	-	10	-	10	-	10	pF

Switching Specifications $C_L = 50pF$, Input t_r , $t_f = 6ns$ (Continued)

		TEST		25°C		-40°C TO 85°C		-55°C TO 125°C			
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Three-State Output Capacitance	C _O	-	-	20	-	20	i	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540, 541)	C _{PD}	C _L = 15pF	5	-	55	-	ī	-	-	-	pF

NOTES:

- 4. C_{PD} is used to determine the dynamic power consumption, per channel.
- 5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where $f_i = Input$ Frequency, $C_L = Output$ Load Capacitance, $V_{CC} = Supply$ Voltage.

Test Circuits and Waveforms

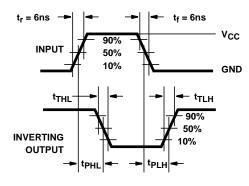


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

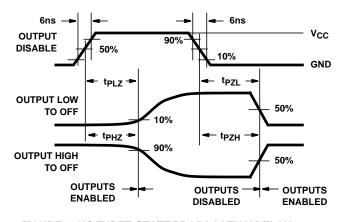


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

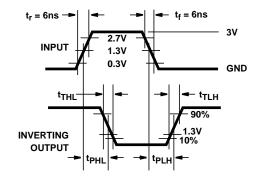


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

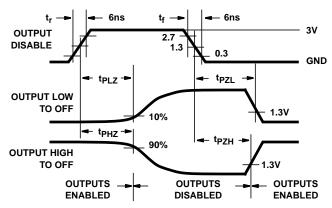
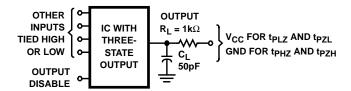


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

Test Circuits and Waveforms (Continued)



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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